

Original Research Article

Addressing Package Voids on Extremely Small Leadframe Device

ABSTRACT

The paper focused in addressing the package voids defect of a semiconductor device utilizing an extremely small leadframe technology. Potential risk analysis and pareto diagram were completed to identify the top reject contributors and eventually come-up with the robust solution. A comprehensive design of experiments (DOE) was done and solution validation was employed to formulate the effective corrective actions. Results revealed that package voids were addressed by optimizing the molding process focusing on the molding temperature and curing time. A significant improvement of 95 % for package voids reduction was achieved. For future works, the parameters and learnings could be used on devices with similar configuration.

Keywords: Mold process; package voids; leadframe; semiconductor; compression molding.

1. INTRODUCTION

New trends and continuous development in semiconductor technology offer great challenges in assembly manufacturing industry. An imperative challenge for any industry is to maintain its competitive market position and value. Important to note that failure to provide customer expectation in terms of quality and time-to-market would result to possible business failure. This critical scenario should really be avoided that is why a line-stressing or risk production is being employed in preparation to full or mass production mode.

The device in focus is a newly-introduced leadframe package in the plant having an extremely small footprint as illustrated in Fig. 1. The device functions as a diode with a single wire connection, for mobile phones and computer applications. Regardless of its simple geometry, it is considered as a device with high complexity as state-of-the-art platforms are needed to satisfy its output process.

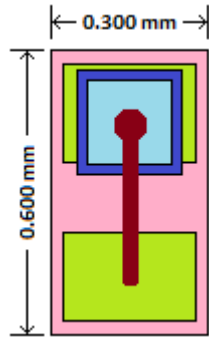


Fig. 1. Device dimension

The device has a very thin die and with the smallest total package dimension. The assembly manufacturing process includes a step cutting method of wafers, compression molding, and in-strip testing, which are not common on other semiconductor industries. A part of the assembly process flow is shown in Fig. 2. Worthy to note that assembly and test process flow varies with the product and the technology [1-3]. With the continuing technology trends and state-of-the-art platforms, challenges in semiconductor assembly manufacturing are inevitable [4-7].

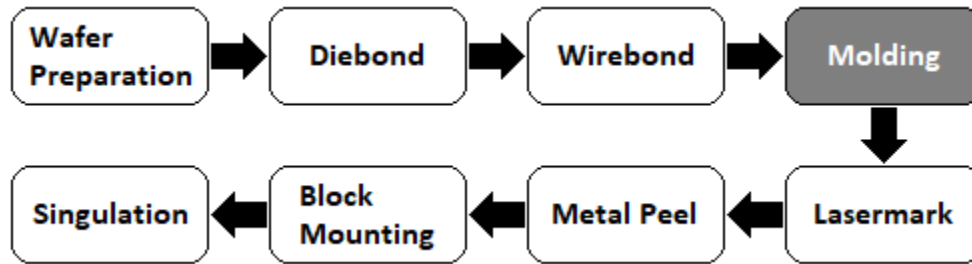


Fig. 2. Assembly process flow

Delinquency in view of customer was the scenario encountered during the line-stressing and ramp-up of the device. Critical processes were identified using risk analysis, and one of which is identified in Table 1 that focused on the molding process. Evaluation was made before the risk build to accelerate confidence on line-stressing. Furthermore, potential risk analysis was given contingency plans and created corrective actions.

Table 1. Potential risk analysis at molding process

Identified risk	Resulting potential risk	Evaluation before action			Identified action
		Probability	Impact	Class	
0.3 mm package molding, package molding defects, voids, incomplete fill	<ul style="list-style-type: none"> ▪Low yield ▪Reliability 	9	9	A	Capability using compression molding technology

Reject contributors on the identified critical processes are shown in Fig. 3. Molding is one critical process identified with deviations or output abnormalities as a result of un-optimized parameters which are normally attributed to newly-introduced devices.

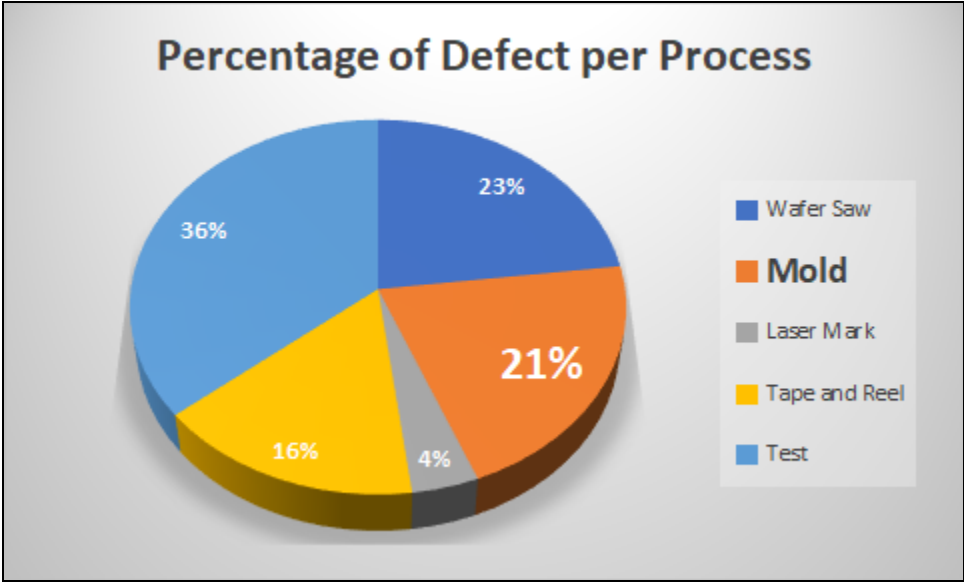


Fig. 3. Defect contribution per assembly process

Of the 21 % defect contribution of the molding process, pareto diagram in Fig. 4 shows package voids as the top reject parts per million (ppm) contributor. Parameter optimization is one of the factors to be checked as the device in focus has no other similar product in the plant as reference. Benchmarking for similar device from other sites is being considered to have a baseline for critical process parameters.

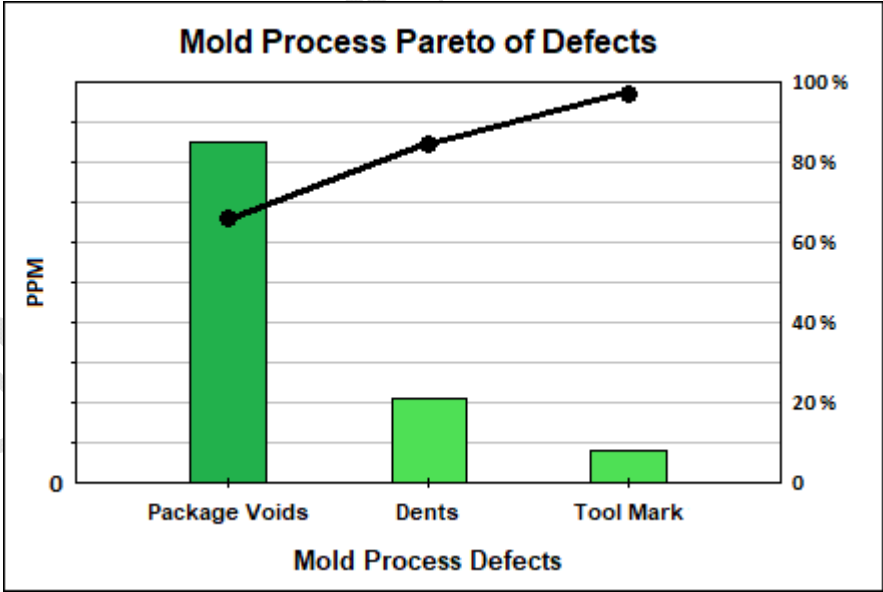
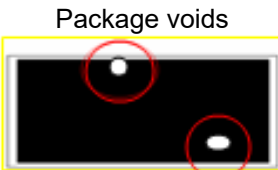


Fig. 4. Pareto diagram of mold process rejects highlighting the top contributor

Top rejects based on pareto diagram substantially affect the yield and delivery during production stressing performance. Henceforth, process optimization is highly recommended

at line-stressing before it reaches the full-production release. Table 2 shows the top defect signature of the molding saw process. Further analysis and investigation of failures were employed by collecting the actual reject samples at this critical process, which are essential in formulating the corrective actions and improvement.

Table 2. Top defect signature of molding process

Critical process	Top Defect signature	Criteria	Remarks
Molding process		Not allowed	Failed

2. LITERATURE REVIEW

One of the integral components in the production of semiconductor devices is the molding compound, a packaging material for encapsulation to protect the device from external environment [8]. Th device uses compression molding shown in Fig. 5 and with ultra-fine filler compound.

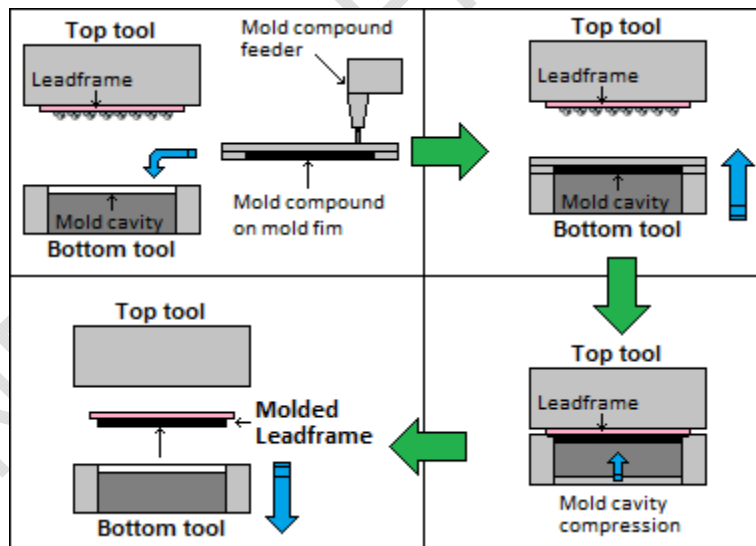


Fig. 5. Compression molding mechanism

The advantages of compression molding system are zero/less wire damage, good filling on narrow gap on die, and no cull/no runner. The technology was necessary for SPPD due to the requirement of narrow mold thickness. With this, device is prone to voids during molding, thus voids became the top reject contributor. Mold voids are commonly easy to correct, but this requires a thorough parameter optimization through design of experiments (commonly referred as DOE). DOE was done to achieve desired parameter range for

molding process considering the critical input and output responses. Moreover, package voids is the critical and primary output response.

3. METHODOLOGY

DOE for compression mold was conducted with the objective to determine and define window for critical parameter range, thus eliminate mold voids. Shown in Fig. 6 is the DOE matrix prepared using a statistical software that automatically provides the combination of runs.

3x3 Factorial		Pattern	MOLD TEMP	CURE TIME	MOLD VOIDS
Design	3x3 Factorial	1 11	170	160	▪
Screening		2 22	175	180	▪
Model		3 12	170	180	▪
		4 13	170	200	▪
		5 23	175	200	▪
		6 32	180	180	▪
Columns (4/0)		7 21	175	160	▪
Pattern		8 33	180	200	▪
MOLD TEMP *		9 31	180	160	▪
CURE TIME *					
MOLD VOIDS *					

Fig. 6. DOE evaluation matrix

Full factorial design with a total of nine runs was created. Using the statistical software tool, mold temperature and cure time were identified as the most critical parameters that will cause mold voids defect. Results of each run are discussed in the succeeding section.

4. RESULTS AND DISCUSSION

During development, the initial problem encountered was package voids every shot. Together with the mold machine field support and the mold compound technical support, DOE was performed using a matrix of different batches of mold compound and sets of mold parameters. The DOE result is illustrated in Fig. 7.

Molding type	Transfer Mold	Compression Mold					
Sample name	-	Sample-2	-	-	-		
EMC name	S240ZF10 (XZ,S)	S240ZF10W (GTL,S)	S240ZF10W (GTL,A)	S240ZF10W -30	S240ZF10W -45		
Epoxy Resin	-	MN Bioheryl					
Hardener	-	LWA-1					
Wax	-	Current	Reduced amount				
Catalyst content	-	Current	Reduced amount				
Flame retardant	-	No					
Anti bubble agent "S"	-	No	Yes	Increased	Yes		
A flexibilizer	-	Yes (0.5)					
Filler Content	vol%wt%	0.5%					
Filler shape	-	All spherical					
Powder sieving	-	No	150um on 1mm pass				
Spiral flow	inch	33	55	55	50	53	
Flash length	mm	1.1	1.7	1.7	1.7	1.4	
Hot hardness(90sec)	-	88	72	72	83	58	
Gelation time(175C)	sec	32	75	50	102	93	
Viscosity(175C)	poise	233	140	140	250	270	
Disk flow	mm	73	94	94	91	91	
Tg	degC	135	135	135	130	125	
CTE	alpha-1	ppm/C	9	7	7	9	7
	alpha-2	ppm/C	30	27	27	30	27
Flexural Modulus	kgf/mm2	2400	2400	2400	2500	2500	
Flexural Strength	kgf/mm2	15	14	15	15	15	
Water absorption	%	0.23	0.23	0.23	0.27	0.28	
Mold shrinkage	%	0.06	0.06	0.06	0.06	0.11	

MA: Multi Aromatic Type
 LWA: Low Water Absorption Type 1
 MF: Multi Functional Type

To reduce surface voids

Need longer cure time such as 175degC/180sec

Fig. 7. DOE matrix for compression molding process optimization

DOE results of compression molding showed that optimum parameters in terms of package voids can be achieved by using the 175°C and 180 seconds curing time regardless of molding compound used.

After the implementation of the identified solutions, level of rejections was monitored. Fig. 8 shows the improvement in the ppm level, before and after the solution implementation. Actual ppm values are intentionally not shown due to confidentiality.

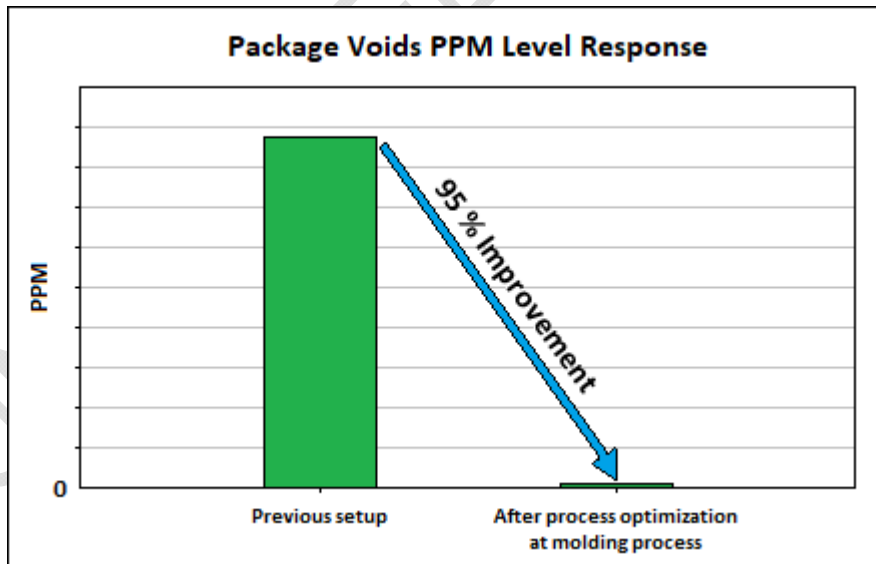


Fig. 8. Improvement after optimization and implementation of corrective actions

An improvement of 95 % for die chippings reduction was achieved through the comprehensive DOE. Assembly yield trend stabilized after the implementation, optimization, and sustainability of the improvement and all corrective actions. This is a good indication of manufacturing preparedness for full-production mode.

5. CONCLUSION AND RECOMMENDATIONS

Comprehensive engineering analyses with the aid of statistical analysis were done in solving and addressing the package voids of an extremely small device at molding process. Through DOE, parameters optimization was formulated, with package voids occurrence significantly minimized by achieving the optimum molding temperature and curing time. A 95 % improvement for package voids reduction was ultimately achieved.

Process optimization plays a vital role to as early as line-stressing stage, before full-production release can be granted. It is important that when newly-introduced devices are coming in, critical processes should be identified and that appropriate improvement, corrective actions, and solutions be made so that when full-production is set, both quality and speed would be achieved. Techniques and learnings shared in this paper could be used for future works on semiconductor devices with comparable configuration.

COMPETING INTERESTS DISCLAIMER:

Authors have declared that no competing interests exist. The products used for this research are commonly and predominantly use products in our area of research and country. There is absolutely no conflict of interest between the authors and producers of the products because we do not intend to use these products as an avenue for any litigation but for the advancement of knowledge. Also, the research was not funded by the producing company rather it was funded by personal efforts of the authors.

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